2D layered transport properties from topological insulator Bi₂Se₃ single crystals and micro flakes O. Chiatti, C. Riha, D. Lawrenz, M. Busch, S. Dusari, J. Sánchez-Barriga, A. Mogilatenko, L. V. Yashina, S. Valencia, A. A. Ünal, O. Rader, S. F. Fischer Sci. Rep. **6**, 27483 (2016).

Short Abstract

Low-field magnetotransport measurements of topological insulators such as Bi2Se3 are important for revealing the nature of topological surface states by quantum corrections to the conductivity, such as weak-antilocalization. Recently, a rich variety of high-field magnetotransport properties in the regime of high electron densities were reported, which can be related to additional two-dimensional layered conductivity, hampering the identification of the topological surface states. Here, we report that quantum corrections to the electronic conduction are dominated by the surface states for a semiconducting case, which can be analyzed by the Hikami-Larkin-Nagaoka model for two coupled surfaces in the case of strong spin-orbit interaction. However, in the metallic-like case this analysis fails and additional two-dimensional contributions need to be accounted for.



Left. (a) Resistivity ρ_{xx} (red curve, left axis) and Hall resistivity ρ_{xy} (blue curve, right axis) vs magnetic field B of the Bi₂Se₃ macro flake with a thickness of t=110 µm at T=0.3 K. (b) Hall conductance per 2D layer $~\widetilde{G}_{_{XY}}{=}G_{_{XY}}{/}Z^{*}$ in units of $e^{2}{/}h$ (red curve, left axis), with measured conductance $G_{xy}=1/R_{xy}$ and Z*=57500, and $d\sigma_{xx}/dB$ (blue curve, right axis) vs inverse magnetic field 1/B at T=0.3 K. The black arrows indicate the QHE plateaux. (c) Landau level (LL) fan diagram at T=0.3 K. The 1/B-positions of the minima and maxima of $\sigma_{xx}(B)$ are shown as a function of the corresponding LL level indices N and N-0.5, respectively. The dashed line represents a linear fit to the data, yielding a slope $B_{\rm f}$ =151 T and an intercept close to zero.